

Vincent LaBella

List of Publications by Year in descending order

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29
papers

495
citations

759233

12
h-index

677142

22
g-index

30
all docs

30
docs citations

30
times ranked

503
citing authors

#	ARTICLE	IF	CITATIONS
1	Spatially Resolved Spin-Injection Probability for Gallium Arsenide. <i>Science</i> , 2001, 292, 1518-1521.	12.6	94
2	Enhancing the Student–Instructor Interaction Frequency. <i>Physics Teacher</i> , 2002, 40, 535-541.	0.3	43
3	Measurement of hot-electron scattering processes at Au/Si(100) Schottky interfaces by temperature-dependent ballistic-electron-emission microscopy. <i>Physical Review B</i> , 1996, 53, 3952-3959.	3.2	40
4	Monte Carlo derived diffusion parameters for Ga on the GaAs(001)-(2 \times 4) surface: A molecular beam epitaxy–scanning tunneling microscopy study. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2000, 18, 1526-1531.	2.1	40
5	Fermi Level Manipulation through Native Doping in the Topological Insulator Bi ₂ Se ₃ . <i>ACS Nano</i> , 2018, 12, 6310-6318.	14.6	37
6	Schottky barrier height measurements of Cu/Si(001), Ag/Si(001), and Au/Si(001) interfaces utilizing ballistic electron emission microscopy and ballistic hole emission microscopy. <i>AIP Advances</i> , 2013, 3, .	1.3	31
7	Reflection high-energy electron diffraction and scanning tunneling microscopy study of InP(001) surface reconstructions. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2000, 18, 1492-1496.	2.1	27
8	Combined molecular beam epitaxy low temperature scanning tunneling microscopy system: Enabling atomic scale characterization of semiconductor surfaces and interfaces. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2005, 23, 1684.	1.6	27
9	Enabling electron diffraction as a tool for determining substrate temperature and surface morphology. <i>Applied Physics Letters</i> , 2001, 79, 3065-3067.	3.3	24
10	Role of As ₄ in Ga diffusion on the GaAs(001)-(2 \times 4) surface: A molecular beam epitaxy-scanning tunneling microscopy study. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1999, 17, 1778.	1.6	22
11	Measurement of the hot electron attenuation length of copper. <i>Applied Physics Letters</i> , 2010, 96, .	3.3	18
12	Time dependent changes in Schottky barrier mapping of the W/Si(001) interface utilizing ballistic electron emission microscopy. <i>Journal of Applied Physics</i> , 2015, 117, .	2.5	12
13	Hot-electron transport studies of the Ag/Si(001) interface using ballistic electron emission microscopy. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2010, 28, 643-646.	2.1	10
14	Nanoscale mapping of the W/Si(001) Schottky barrier. <i>Journal of Applied Physics</i> , 2014, 116, 023705.	2.5	9
15	A UNION OF THE REAL-SPACE AND RECIPROCAL-SPACE VIEW OF THE GaAs(001) SURFACE. <i>International Journal of Modern Physics B</i> , 2001, 15, 2301-2333.	2.0	8
16	Signatures of the semiconductor crystallographic orientation on the charge transport across non-epitaxial diodes. <i>Applied Physics Letters</i> , 2012, 100, .	3.3	8
17	Relating spatially resolved maps of the Schottky barrier height to metal/semiconductor interface composition. <i>Journal of Applied Physics</i> , 2016, 119, .	2.5	7
18	Microscopic structure of spontaneously formed islands on the GaAs(001)-(2 \times 4) reconstructed surface. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2001, 19, 1640.	1.6	6

#	ARTICLE	IF	CITATIONS
19	Nanoscale Schottky barrier mapping of thermally evaporated and sputter deposited W/Si(001) diodes using ballistic electron emission microscopy. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2016, 34, .	1.2	6
20	Detection of silicide formation in nanoscale visualization of interface electrostatics. Applied Physics Letters, 2017, 110, 141606.	3.3	6
21	Efficient circuit design for low power energy harvesting. AIP Advances, 2020, 10, .	1.3	6
22	Pulsed-N ₂ assisted growth of 5-20 nm thick W films. AIP Advances, 2015, 5, .	1.3	4
23	Synthesis and properties of ferromagnetic nanostructures embedded within a high-quality crystalline silicon matrix via ion implantation and nanocavity assisted gettering processes. Journal of Applied Physics, 2014, 116, 054306.	2.5	3
24	Nanoscale Schottky barrier visualization utilizing computational modeling and ballistic electron emission microscopy. Journal of Applied Physics, 2018, 123, .	2.5	3
25	Mapping the Spin-Injection Probability on the Atomic Scale. Journal of Superconductivity and Novel Magnetism, 2002, 15, 37-42.	0.5	1
26	Magnetic and Structural Properties of Mn-implanted Si. Materials Research Society Symposia Proceedings, 2004, 853, 114.	0.1	1
27	Visualizing metal/HfO ₂ /SiO ₂ /Si(001) interface electrostatic barrier heights with ballistic hole emission microscopy. Journal of Applied Physics, 2019, 126, 195302.	2.5	1
28	Determination of the energetic resolution of Schottky barrier visualization via interface band structure and parallel momentum conservation. AIP Advances, 2021, 11, .	1.3	1
29	Simultaneous surface topography and spin-injection probability. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2003, 21, 67.	1.6	0